

# 2SK2278L, 2SK2278S

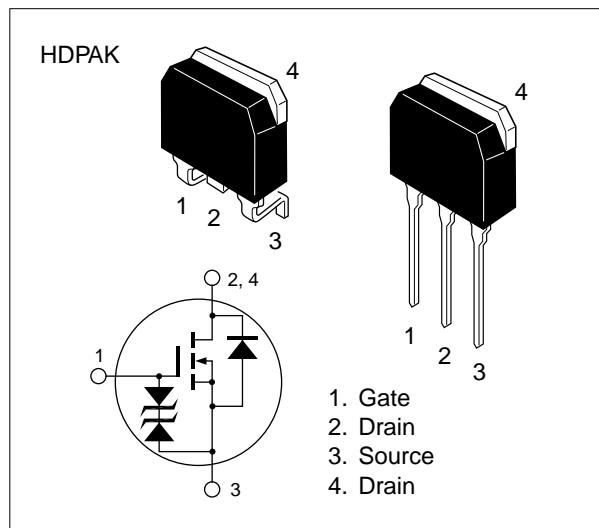
## Silicon N Channel MOS FET

### Application

High speed power switching

### Features

- High breakdown voltage ( $V_{DSS} = 1500$  V)
- High speed switching
- No secondary breakdown
- Suitable for Switching regulator, DC – DC converter



**Table 1 Absolute Maximum Ratings (Ta = 25°C)**

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	1500	V
Gate to source voltage	$V_{GSS}$	$\pm 20$	V
Drain current	$I_D$	2.5	A
Drain peak current	$I_{D(\text{pulse})}^*$	7	A
Body-drain diode reverse drain current	$I_{DR}$	2.5	A
Channel dissipation	$P_{ch}^{**}$	100	W
Channel temperature	$T_{ch}$	150	°C
Storage temperature	$T_{stg}$	-55 to +150	°C

\* PW ≤ 10 μs, duty cycle ≤ 1 %

\*\* Value at  $T_c = 25$  °C

2SK2278 (L), 2SK2278 (S)

**Table 2 Electrical Characteristics (Ta = 25°C)**

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	1500	—	—	V	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0
Gate to source leak current	I <sub>GSS</sub>	—	—	±1	μA	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0
Zero gate voltage drain current	I <sub>DSS</sub>	—	—	500	μA	V <sub>DS</sub> = 1200 V, V <sub>GS</sub> = 0
Gate to source cutoff voltage	V <sub>GS(off)</sub>	2.0	—	4.0	V	I <sub>D</sub> = 1 mA, V <sub>DS</sub> = 10 V
Static drain to source on state resistance	R <sub>DS(on)</sub>	—	9	12	Ω	I <sub>D</sub> = 2 A V <sub>GS</sub> = 15 V *
Forward transfer admittance	y <sub>fs</sub>	0.45	0.75	—	S	I <sub>D</sub> = 1 A V <sub>DS</sub> = 20 V *
Input capacitance	C <sub>iss</sub>	—	990	—	pF	V <sub>DS</sub> = 10 V
Output capacitance	C <sub>oss</sub>	—	125	—	pF	V <sub>GS</sub> = 0
Reverse transfer capacitance	C <sub>rss</sub>	—	60	—	pF	f = 1 MHz
Turn-on delay time	t <sub>d(on)</sub>	—	17	—	ns	I <sub>D</sub> = 2 A
Rise time	t <sub>r</sub>	—	70	—	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	t <sub>d(off)</sub>	—	110	—	ns	R <sub>L</sub> = 15 Ω
Fall time	t <sub>f</sub>	—	60	—	ns	
Body-drain diode forward voltage	V <sub>DF</sub>	—	0.9	—	V	I <sub>F</sub> = 2 A, V <sub>GS</sub> = 0
Body-drain diode reverse recovery time	t <sub>rr</sub>	—	1750	—	μs	I <sub>F</sub> = 2 A, V <sub>GS</sub> = 0, diF / dt = 100 A / μs

\* Pulse Test

See characteristic curves of 2SK1317.

